

# TLP250

Transistor Inverter  
 Inverter For Air Conditionor  
 IGBT Gate Drive  
 Power MOS FET Gate Drive

The TOSHIBA TLP250 consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

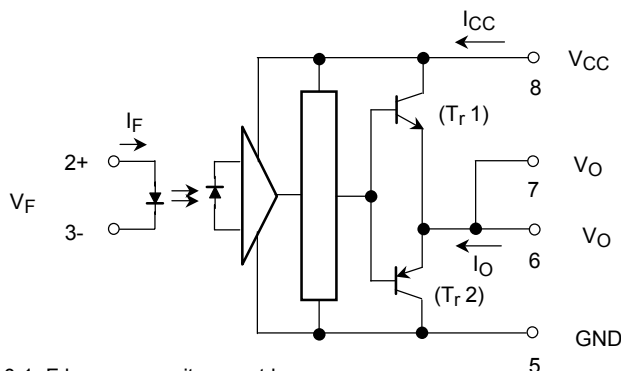
TLP250 is suitable for gate driving circuit of IGBT or power MOS FET.

- Input threshold current:  $I_F=5\text{mA}(\text{max.})$
- Supply current ( $I_{CC}$ ):  $11\text{mA}(\text{max.})$
- Supply voltage ( $V_{CC}$ ):  $10\text{--}35\text{V}$
- Output current ( $I_O$ ):  $\pm 1.5\text{A}(\text{max.})$
- Switching time ( $t_{pLH}/t_{pHL}$ ):  $1.5\mu\text{s}(\text{max.})$
- Isolation voltage:  $2500V_{\text{rms}}(\text{min.})$
- UL recognized: UL1577, file No.E67349
- Option (D4) type  
 VDE approved: DIN VDE0884/06.92,certificate No.76823  
 Maximum operating insulation voltage: 630VPK  
 Highest permissible over voltage: 4000VPK

**(Note) When a VDE0884 approved type is needed, please designate the "option (D4)"**

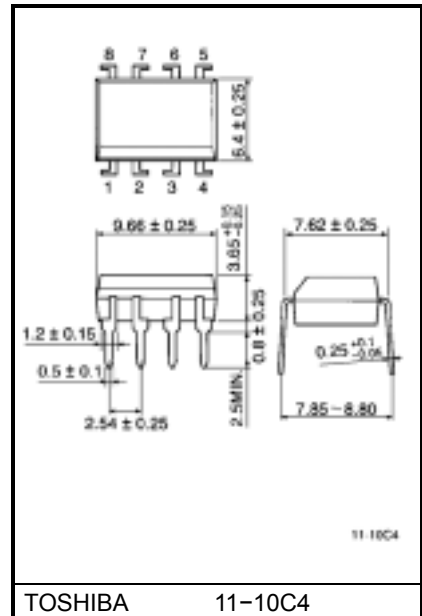
- Creepage distance: 6.4mm(min.)  
 Clearance: 6.4mm(min.)

## Schematic



A 0.1 $\mu\text{F}$  bypass capacitor must be connected between pin 8 and 5 (See Note 5).

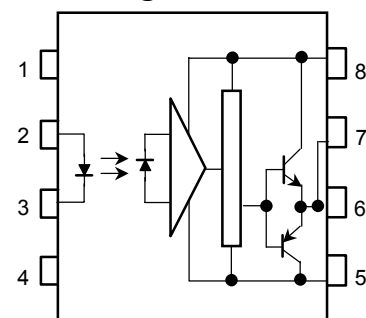
Unit in mm



TOSHIBA 11-10C4

Weight: 0.54 g

## Pin Configuration (top view)



- 1 : N.C.
- 2 : Anode
- 3 : Cathode
- 4 : N.C.
- 5 : GND
- 6 :  $V_O$  (Output)
- 7 :  $V_O$
- 8 :  $V_{CC}$

## Truth Table

		Tr1	Tr2
Input LED	On	On	Off
	Off	Off	On

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
LED	Forward current	$I_F$	20	mA	
	Forward current derating (Ta ≥ 70°C)	$\Delta I_F / \Delta T_a$	-0.36	mA / °C	
	Peak transient forward current (Note 1)	$I_{FPT}$	1	A	
	Reverse voltage	$V_R$	5	V	
	Junction temperature	$T_j$	125	°C	
Detector	"H" peak output current ( $P_W \leq 2.5\mu s, f \leq 15kHz$ ) (Note 2)	$I_{OPH}$	-1.5	A	
	"L" peak output current ( $P_W \leq 2.5\mu s, f \leq 15kHz$ ) (Note 2)	$I_{OPL}$	+1.5	A	
	Output voltage	(Ta ≤ 70°C)	$V_O$	35	V
		(Ta = 85°C)		24	
	Supply voltage	(Ta ≤ 70°C)	$V_{CC}$	35	V
		(Ta = 85°C)		24	
	Output voltage derating (Ta ≥ 70°C)		$\Delta V_O / \Delta T_a$	-0.73	V / °C
	Supply voltage derating (Ta ≥ 70°C)		$\Delta V_{CC} / \Delta T_a$	-0.73	V / °C
	Junction temperature		$T_j$	125	°C
Operating frequency (Note 3)		f	25	kHz	
Operating temperature range		$T_{opr}$	-20~85	°C	
Storage temperature range		$T_{stg}$	-55~125	°C	
Lead soldering temperature (10 s) (Note 4)		$T_{sol}$	260	°C	
Isolation voltage (AC, 1 min., R.H. ≤ 60%) (Note 5)		$BV_S$	2500	Vrms	

Note 1: Pulse width  $P_W \leq 1\mu s$ , 300pps

Note 2: Exponential waveform

Note 3: Exponential waveform,  $I_{OPH} \leq -1.0A (\leq 2.5\mu s)$ ,  $I_{OPL} \leq +1.0A (\leq 2.5\mu s)$

Note 4: It is 2 mm or more from a lead root.

Note 5: Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Note 6: A ceramic capacitor (0.1μF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1cm.

## Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Input current, on (Note 7)	$I_{F(ON)}$	7	8	10	mA
Input voltage, off	$V_{F(OFF)}$	0	—	0.8	V
Supply voltage	$V_{CC}$	15	—	30   20	V
Peak output current	$I_{OPH}/I_{OPL}$	—	—	±0.5	A
Operating temperature	$T_{opr}$	-20	25	70   85	°C

Note 7: Input signal rise time (fall time) < 0.5 μs.

## Electrical Characteristics (Ta = -20~70°C, unless otherwise specified)

Characteristic		Symbol	Test Circuit	Test Condition	Min.	Typ.*	Max.	Unit	
Input forward voltage		V <sub>F</sub>	—	I <sub>F</sub> = 10 mA, Ta = 25°C		1.6	1.8	V	
Temperature coefficient of forward voltage		ΔV <sub>F</sub> / ΔTa	—	I <sub>F</sub> = 10 mA	—	-2.0	—	mV / °C	
Input reverse current		I <sub>R</sub>	—	V <sub>R</sub> = 5V, Ta = 25°C		—	10	μA	
Input capacitance		C <sub>T</sub>	—	V = 0, f = 1MHz, Ta = 25°C	—	45	250	pF	
Output current	"H" level	I <sub>OPH</sub>	3	V <sub>CC</sub> = 30V (*1)	I <sub>F</sub> = 10 mA V <sub>8-6</sub> = 4V	-0.5	-1.5	—	A
	"L" level	I <sub>OPL</sub>	2		I <sub>F</sub> = 0 V <sub>6-5</sub> = 2.5V	0.5	2	—	
Output voltage	"H" level	V <sub>OH</sub>	4	V <sub>CC1</sub> = +15V, V <sub>EE1</sub> = -15V R <sub>L</sub> = 200Ω, I <sub>F</sub> = 5mA	11	12.8	—	V	
	"L" level	V <sub>OL</sub>	5	V <sub>CC1</sub> = +15V, V <sub>EE1</sub> = -15V R <sub>L</sub> = 200Ω, V <sub>F</sub> = 0.8V	—	-14.2	-12.5		
Supply current	"H" level	I <sub>CCH</sub>	—	V <sub>CC</sub> = 30V, I <sub>F</sub> = 10mA Ta = 25°C	—	7	—	mA	
				V <sub>CC</sub> = 30V, I <sub>F</sub> = 10mA	—	—	11		
	"L" level	I <sub>CCL</sub>	—	V <sub>CC</sub> = 30V, I <sub>F</sub> = 0mA Ta = 25°C	—	7.5	—		
				V <sub>CC</sub> = 30V, I <sub>F</sub> = 0mA	—	—	11		
Threshold input current	"Output L→H"	I <sub>FLH</sub>	—	V <sub>CC1</sub> = +15V, V <sub>EE1</sub> = -15V R <sub>L</sub> = 200Ω, V <sub>O</sub> > 0V	—	1.2	5	mA	
Threshold input voltage	"Output H→L"	I <sub>FHL</sub>	—	V <sub>CC1</sub> = +15V, V <sub>EE1</sub> = -15V R <sub>L</sub> = 200Ω, V <sub>O</sub> < 0V	0.8	—	—	V	
Supply voltage		V <sub>CC</sub>	—		10	—	35	V	
Capacitance (input-output)		C <sub>S</sub>	—	V <sub>S</sub> = 0, f = 1MHz Ta = 25	—	1.0	2.0	pF	
Resistance(input-output)		R <sub>S</sub>	—	V <sub>S</sub> = 500V, Ta = 25°C R.H. ≤ 60%	1×10 <sup>12</sup>	10 <sup>14</sup>	—	Ω	

\* All typical values are at Ta = 25°C (\*1): Duration of I<sub>O</sub> time ≤ 50μs

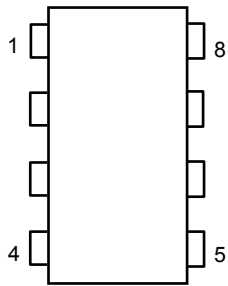
## Switching Characteristics (Ta = -20~70°C , unless otherwise specified)

Characteristic	Symbol	Test Circuit	Test Condition	Min.	Typ.*	Max.	Unit
Propagation delay time	L→H	t <sub>pLH</sub>	I <sub>F</sub> = 8mA (Note 7) V <sub>CC1</sub> = +15V, V <sub>EE1</sub> = -15V R <sub>L</sub> = 200Ω	—	0.15	0.5	μs
	H→L	t <sub>pHL</sub>		—	0.15	0.5	
Output rise time	t <sub>r</sub>	6		—	—	—	
Output fall time	t <sub>f</sub>			—	—	—	
Common mode transient immunity at high level output	C <sub>MH</sub>	7	V <sub>CM</sub> = 600V, I <sub>F</sub> = 8mA V <sub>CC</sub> = 30V, Ta = 25°C	-5000	—	—	V / μs
Common mode transient immunity at low level output	C <sub>ML</sub>	7	V <sub>CM</sub> = 600V, I <sub>F</sub> = 0mA V <sub>CC</sub> = 30V, Ta = 25°C	5000	—	—	V / μs

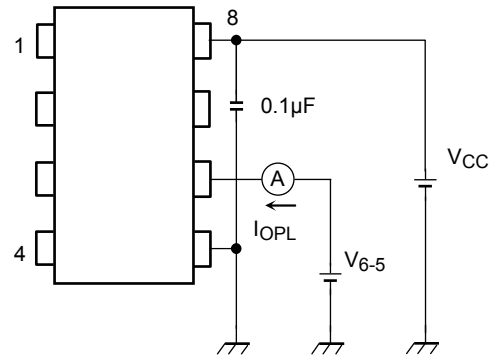
\* All typical values are at Ta = 25°C

Note 7: Input signal rise time (fall time) < 0.5 μs.

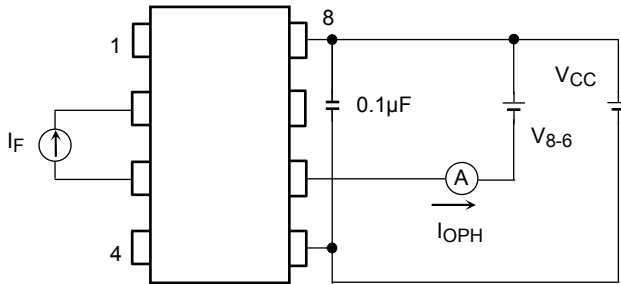
Test Circuit 1 :



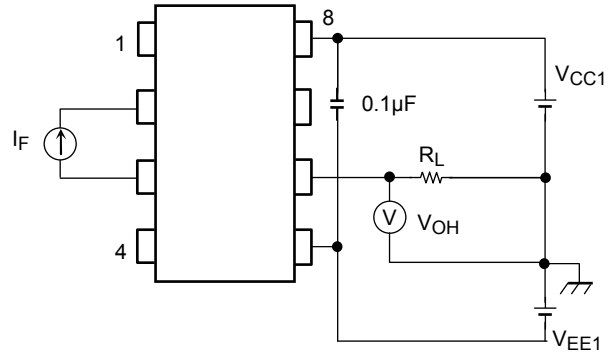
Test Circuit 2 : IOPL



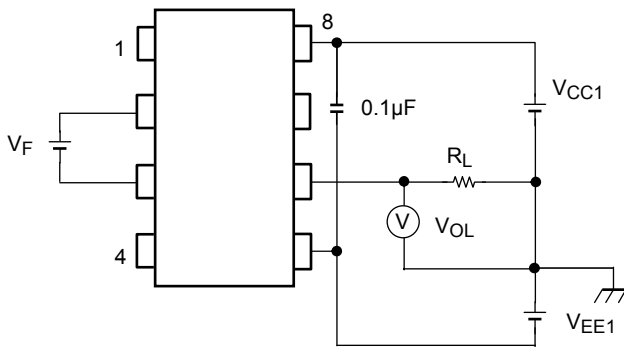
Test Circuit 3 : IOPH



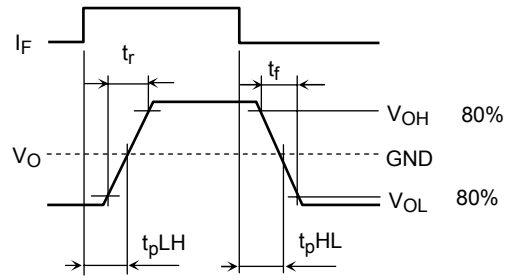
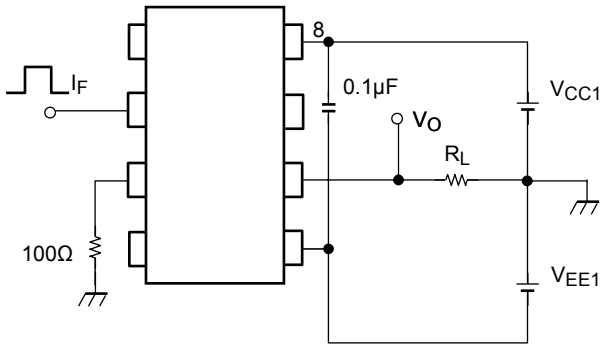
Test Circuit 4 : VOH



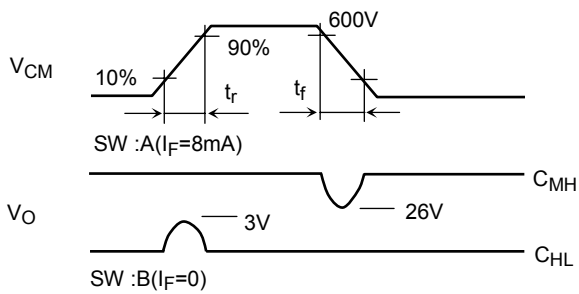
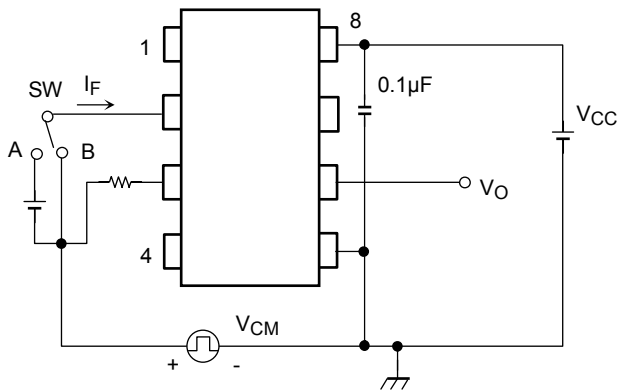
Test Circuit 5 : VOL



Test Circuit 6:  $t_{pLH}$ ,  $t_{pHL}$ ,  $t_r$ ,  $t_f$



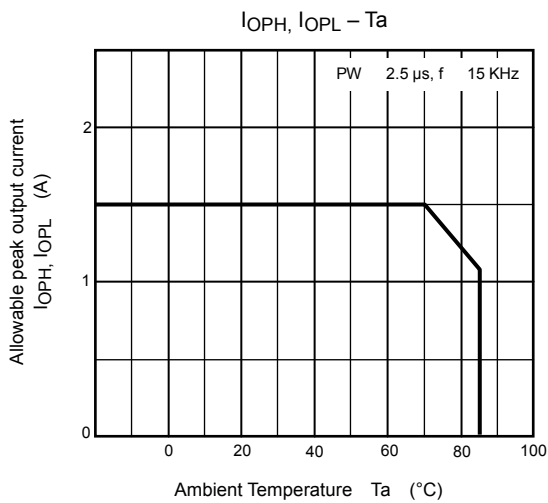
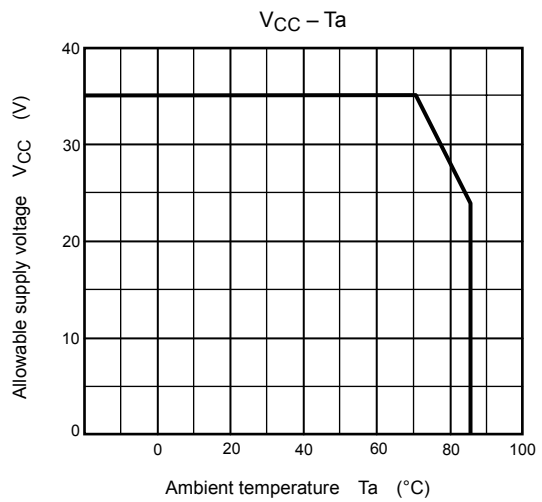
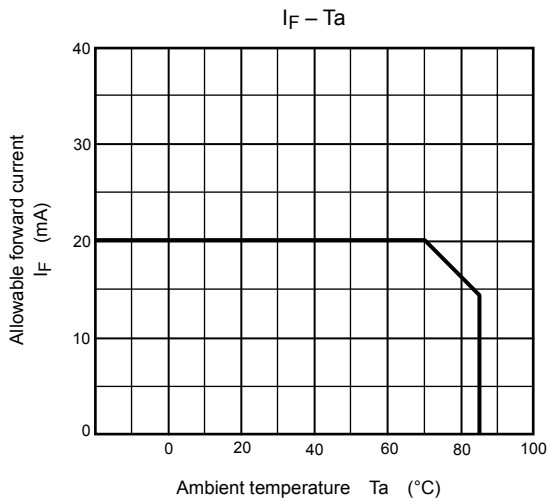
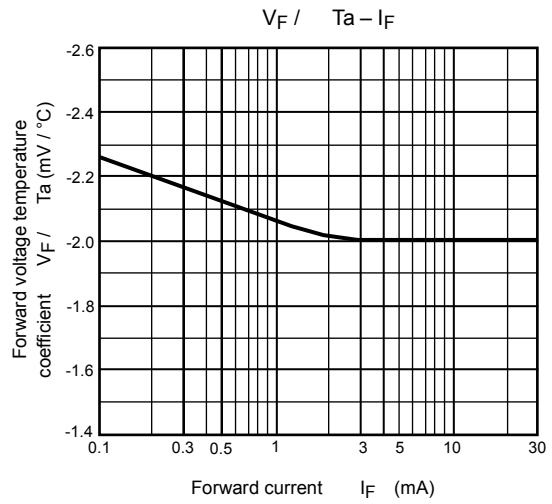
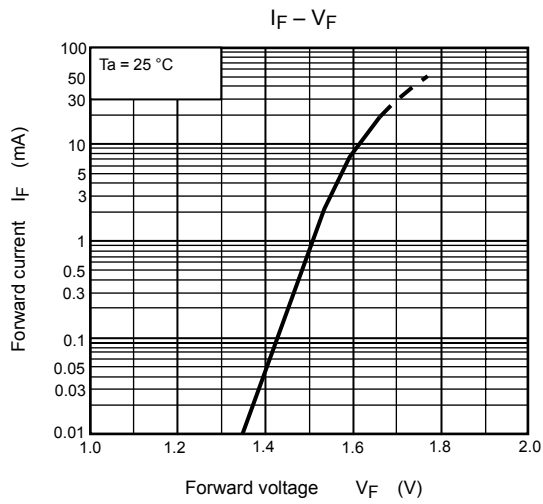
Test Circuit 7:  $C_{MH}$ ,  $C_{ML}$



$$C_{ML} = \frac{480 \text{ (V)}}{t_r \text{ (\mu s)}}$$

$$C_{MH} = \frac{480 \text{ (V)}}{t_f \text{ (\mu s)}}$$

$C_{ML}(C_{MH})$  is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.



**RESTRICTIONS ON PRODUCT USE**

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.  
In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.